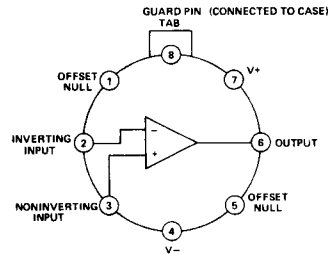


FEATURES

- Low Offset Voltage: 0.5mV max (AD545L),
0.25mV max (AD545M)
- Low Offset Voltage Drift: 5 μ V/ $^{\circ}$ C max (AD545L),
3 μ V/ $^{\circ}$ C max (AD545M)
- Low Power: 1.5mA max
- Low Bias Current: 1pA max (AD545K, L, M)
- Low Noise: 3 μ V p-p, 0.1 to 10Hz

AD545 FUNCTIONAL BLOCK DIAGRAM



TO-99
TOP VIEW

PRODUCT DESCRIPTION

The AD545 is a precision FET-input operational amplifier with overall performance far superior to the general purpose IC FET-input op amp. The device is fabricated using a low leakage FET paired with a low power op amp. Bias current is specified as 2pA max for the AD545J and 1pA max for the AD545K, L and M. Offset voltage is laser trimmed to 0.5mV max for the AD545L, 0.25mV max for the AD545M. All devices also feature low voltage noise and power consumption. The AD545 is internally compensated, short circuit protected and free of latch-up.

The AD545 series offers a broad combination of performance features previously unavailable from a single device. For precision applications the AD545M specifies a 0.25mV max offset voltage, 3 μ V/ $^{\circ}$ C max drift and 1pA max bias current. The AD545J, with a 1mV max offset voltage, 25 μ V/ $^{\circ}$ C max drift and 2pA max bias current, is the best price performance choice.

These devices are recommended for a variety of general purpose and precision applications requiring low bias currents and high input impedance such as pH/plon sensitive electrodes, photo-current detectors, biological microprobes, long term precision integrators and vacuum iongauge measurements. The versatility of the AD545 is further enhanced by its excellent low frequency noise (3 μ V p-p, 0.1 to 10Hz) and low power consumption (1.5mA max) for portable applications.

As with previous electrometer amplifier designs from Analog Devices, the case is guarded thus minimizing stray leakage. This feature will also shield the input circuitry from external noise and supply transients, as well as reducing common mode input capacitance from 0.8pF to 0.2pF.

The AD545 is available in four versions of bias current and offset voltage, the "J", "K", "L", and "M". All are specified from 0 to +70 $^{\circ}$ C and supplied in a hermetically sealed TO-99 package.

PRODUCT HIGHLIGHTS

1. The offset voltage on the AD545 is laser trimmed to a level typically less than 250 μ V. Offset voltage drift is significantly lower than previously available FET-input devices (3 μ V/ $^{\circ}$ C max for the AD545M). If additional external nulling is desired, the effect on drift is minimal (approximately 3 μ V/ $^{\circ}$ C per millivolt, nulled).
2. Bias current is specified as the maximum measured at either input with the device fully warmed up on \pm 15V supplies at +25 $^{\circ}$ C ambient.
3. The low quiescent current drain of 0.8mA typical, and 1.5mA max, is among the lowest of any IC op amp and keeps self heating to a minimum.
4. The combination of low input noise voltage and very low input noise current is such that for source impedances from much over one megohm up to 10¹¹ ohm, the Johnson noise of the source will easily dominate the noise characteristics.

SPECIFICATIONS (typical @ +25°C with $V_S = \pm 15V$ dc, unless otherwise specified)

MODEL	AD545J	AD545K	AD545L	AD545M
OPEN LOOP GAIN¹				
$V_{OUT} = \pm 10V, R_L \geq 2k\Omega$	20,000V/V min	40,000V/V min	40,000V/V min	40,000V/V min
$R_L \geq 10k\Omega$	40,000V/V min	50,000V/V min	50,000V/V min	50,000V/V min
$T_A = \text{min to max } R_L \geq 2k\Omega$	15,000V/V min	25,000V/V min	40,000V/V min	40,000V/V min
OUTPUT CHARACTERISTICS				
Voltage @ $R_L = 2k\Omega, T_A = \text{min to max}$	$\pm 10V$ min ($\pm 12V$ typ)	*	*	*
@ $R_L = 10k\Omega, T_A = \text{min to max}$	$\pm 12V$ min ($\pm 13V$ typ)	*	*	*
Load Capacitance ²	500pF	*	*	*
Short Circuit Current	10mA min (25mA typ)	*	*	*
FREQUENCY RESPONSE				
Unity Gain, Small Signal	700kHz	*	*	*
Full Power Response	5kHz min (16kHz typ)	*	*	*
Slew Rate Inverting Unity Gain	0.3V/ μ s min (1.0V/ μ s typ)	*	*	*
Overload Recovery Inverting Unity Gain	100 μ s max (16 μ s typ)	*	*	*
INPUT OFFSET VOLTAGE³				
vs. Temperature, $T_A = \text{min to max}$	1.0mV max	1.0mV max	0.5mV max	0.25mV max
vs. Supply, $T_A = \text{min to max}$	25 μ V/ $^{\circ}$ C max	15 μ V/ $^{\circ}$ C max	5 μ V/ $^{\circ}$ C max	3 μ V/ $^{\circ}$ C max
vs. Supply, $T_A = \text{min to max}$	400 μ V/V max (50 μ V/V typ)	200 μ V/V max	200 μ V/V max	200 μ V/V max
INPUT BIAS CURRENT				
Either Input ⁴	2pA max	1pA max	1pA max	1pA max
INPUT IMPEDANCE				
Differential	1.6pF 10 ¹³ Ω	*	*	*
Common Mode	0.8pF 10 ¹⁴ Ω	*	*	*
INPUT NOISE				
Voltage, 0.1Hz to 10Hz	3.0 μ V (p-p)	*	*	5 μ V (p-p) max
f = 10Hz	55nV/ $\sqrt{\text{Hz}}$	*	*	*
f = 100Hz	45nV/ $\sqrt{\text{Hz}}$	*	*	*
f = 1kHz	35nV/ $\sqrt{\text{Hz}}$	*	*	*
Current, 0.1 to 10Hz	0.01pA (p-p)	*	*	*
10Hz to 10kHz	0.03pA rms	*	*	*
INPUT VOLTAGE RANGE				
Differential	$\pm 20V$ min	*	*	*
Common Mode, $T_A = \text{min to max}$	$\pm 10V$ min ($\pm 12V$ typ)	*	*	*
Common Mode Rejection, $V_{IN} = \pm 10V$	66dB min (80dB typ)	70dB min	76dB min	76dB min
Maximum Safe Input Voltages ⁵	$\pm V_S$	*	*	*
POWER SUPPLY				
Rated Performance	$\pm 15V$ typ	*	*	*
Operating	$\pm 5V$ min ($\pm 18V$ max)	*	*	*
Quiescent Current	1.5mA max (0.8mA typ)	*	*	*
TEMPERATURE				
Operating, Rated Performance	0 to +70 $^{\circ}$ C	*	*	*
Storage	-65 $^{\circ}$ C to +150 $^{\circ}$ C	*	*	*
PACKAGE OPTION⁶				
TO-99 Style (H08B)	AD545JH	AD545KH	AD545LH	AD545MH

*Specifications same as AD545J.

NOTES

¹ Open Loop Gain is specified with or without nulling of V_{OS} .

² A conservative design would not exceed 500pF of load capacitance.

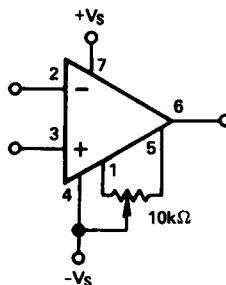
³ Input Offset Voltage specifications are guaranteed after 5 minutes of operation at $T_A = +25^{\circ}\text{C}$.

⁴ Bias Current specifications are guaranteed after 5 minutes of operation at $T_A = +25^{\circ}\text{C}$. For higher temperatures, the current doubles every +10 $^{\circ}\text{C}$.

⁵ If it is possible for the input voltage to exceed the supply voltage, a series protection resistor should be added to limit input current to 0.5mA. The input devices can handle overload currents of 0.5mA indefinitely without damage.

⁶ See Section 19 for package outline information.

Specifications subject to change without notice.



Standard Offset Null Circuit

LAYOUT AND CONNECTION CONSIDERATIONS

The design of very high impedance measurement systems introduces a new level of problems associated with the reduction of leakage paths and noise pickup.

1. A primary consideration in high impedance system designs is to attempt to place the measuring device as near to the signal source as possible. This will minimize current leakage paths, noise pickup and capacitive loading.
2. The use of guarding techniques is essential to realizing the capability of the low input bias currents of the AD545. Guarding is achieved by applying a low impedance bootstrap potential to the outside of the insulation material surrounding the high impedance signal line. This bootstrap potential is held at the same level as that of the high impedance line; therefore, there is no voltage drop across the insulation, and hence, no leakage. The guard will also act as a shield to reduce noise pickup and serves the additional function of reducing the effective capacitance to the input line. The case of the AD545 is brought out separately to pin 8 so that it can also be connected to the guard potential. This technique virtually eliminates potential leakage paths across the package insulation, provides a noise shield for the sensitive circuitry, and reduces common-mode input capacitance to about 0.2pF. Figure 10 shows a proper printed circuit board layout for input guarding and connecting the case guard. Figures 2 and 3 show guarding connections for typical inverting and non-inverting applications. If pin 8 is not used for guarding, it should be connected to ground or one of the amplifier's power supplies to reduce noise.
3. Printed circuit board layout and construction is critical in achieving low leakage performance. The best performance will be realized by using a teflon IC socket for the AD545 but at least a teflon stand-off should be used for the high-impedance lead. If this is not feasible, the input guarding scheme shown in Figure 10 will minimize leakage as much as possible and should be applied to both sides of the board. The guard ring is connected to a low impedance potential at

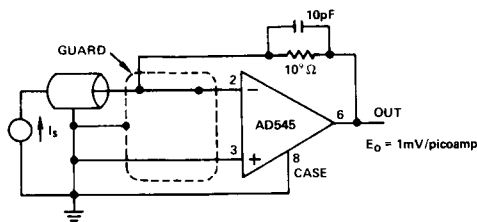


Figure 1. Picoampere Current-to-Voltage Converter Inverting Configuration

the same level as the inputs. High impedance signal lines should not be extended for any unnecessary length on a printed circuit; to minimize noise and leakage, they must be carried in rigid, shielded cables.

APPLICATION NOTES

The AD545 offers one of the lowest input bias currents available in an integrated circuit package. Performing accurate measurements with this device requires careful attention to detail; the notes given here will aid the user in realizing the full measurement potential of the AD545 and extending its performance limits.

1. As with all junction FET input devices, the temperature of the FET's themselves is all-important in determining the input bias currents. Over the operating temperature range, the input bias currents closely follow a characteristic of doubling every 10°C; therefore, every effort should be made to minimize device operating temperature.
2. The heat dissipation can be reduced initially by careful investigation of the application. First, if possible, reduce the required power supplies, since internal power consumption contributes the largest component of self-heating. The effects of this are shown in Figure 7, which shows typical input bias current and quiescent current versus supply voltage.
3. Output loading effects, which are normally ignored, can cause a significant increase in chip temperature and therefore bias current. For example, a 2kΩ load driven at 10 volts at the output will cause at least an additional 25 milliwatts dissipation in the output stage (and some in other stages) over the typical 24 milliwatts, thereby at least doubling the effects of self-heating. The results of this form of additional power dissipation are demonstrated in Figure 9, which shows normalized input bias current versus additional power dissipated (it doubles every 10°C); we recommend restricting the load impedance to be at least 10kΩ.

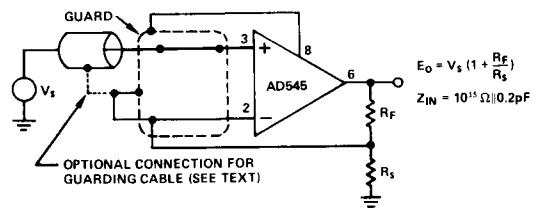


Figure 2. Very High Impedance Non-Inverting Amplifier

Typical Performance Curves

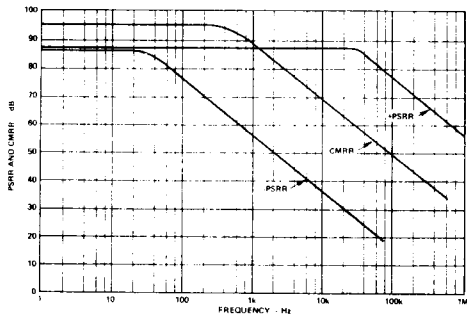


Figure 3. PSRR and CMRR Versus Frequency

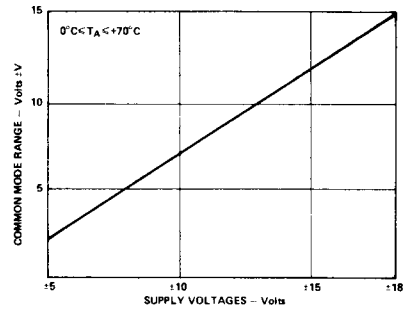


Figure 4. Input Common Mode Range Versus Supply Voltage

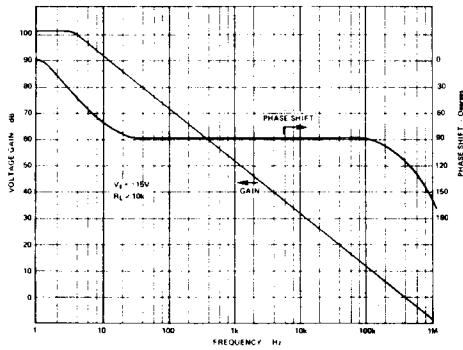


Figure 5. Open Loop Frequency Response

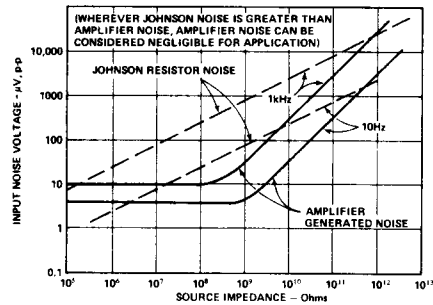


Figure 6. Total Input Noise Voltage Versus Source Impedance and Bandwidth

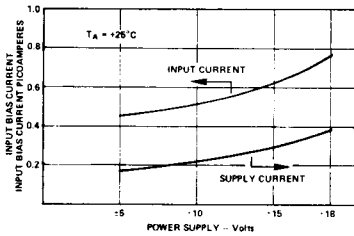


Figure 7. Input Bias Current and Supply Current Versus Supply Voltage

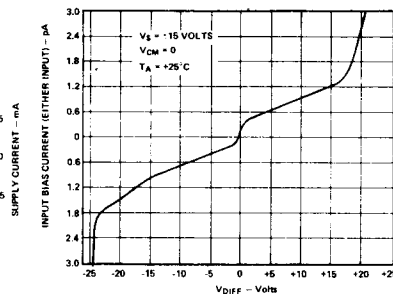


Figure 8. Input Bias Current Versus Differential Input Voltage

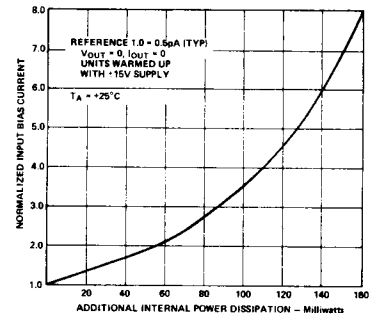


Figure 9. Input Bias Current Versus Additional Power Dissipation

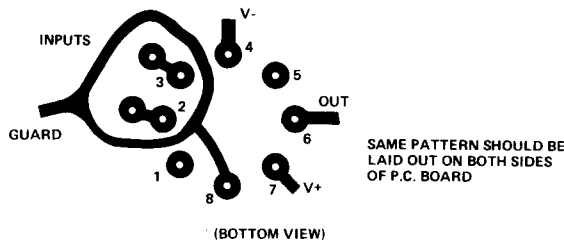


Figure 10. Board Layout for Guarding Inputs with Guarded TO-99 Package